

| 1N5614 | S2M |
|--------|-----|
| 1N5616 | S4M |
| 1N5618 | S6M |
| 1N5620 | S8M |
| 1N5622 | S0M |

January 7, 1998

TEL:805-498-2111 FAX:805-498-3804 WEB:http://www.semtech.com

QUICK REFERENCE AXIAL LEADED HERMETICALLY SEALED DATA STANDARD RECOVERY RECTIFIER DIODE

- = 2.0A
 - V_R = 200 1000V Low reverse leakage current
 - Hermetically sealed in Metoxilite fused metal oxide
- $t_{rr} = 2\mu S$

F

- Good thermal shock resistance
- $V_{\rm F} = 1.1V$
- Low forward voltage drop Avalanche capability. ٠

ABSOLUTE MAXIMUM RATINGS (@ 25°C unless otherwise specified)

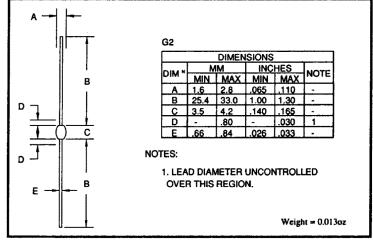
| | Symbol | 1N5614 1N5616 1N5618 1N5620 1N5622 Unit S2M S4M S6M S8M S0M |
|--|--------------------|--|
| Working reverse voltage | VRWM | 200 400 600 800 1000 V |
| Repetitive reverse voltage | VRRM | 200 400 600 800 1000 V |
| Average forward current (@ 55°C, lead length 0.375") | I _{F(AV)} | ← 2.0 → A |
| Repetitive surge current (@ 55°C in free air, lead length 0.375") | I _{FRM} | ← 10 → A |
| Non-repetitive surge current ($t_p = 8.3mS$, $@V_R \& T_{jmax}$) | I _{FSM} | ← 30 → A |
| Storage temperature range | TSTG | ← -65 to +175 → °C |
| Operating temperature range | TOP | ← -65 to +175 → °C |

These products are qualified to MIL-PRF-19500/427 and are preferred parts as listed in MIL-STD-701. They can be

JANTXV and JANS versions. These products are available in Europe to DEF STAN 59-61 (PART 80)/029 to F and FX levels.

supplied fully released as JAN, JANTX,







RECTIFIER, up to 1kV, 2A, 2µs

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CHARACTERISTICS (@ 25^oC unless otherwise specified)

| | Symbol | 1N5614 1N5616 1N5618 1N5620 1N5622 S2M S4M S6M S8M S0M | Unit |
|--|--|---|------------------|
| Average forward current (sine wave) - max. pcb mounted; $T_A = 55^{\circ}C$ - max. L = 3/8"; $T_L = 55^{\circ}C$ | I _{F(AV)} I _{F(AV)} | ↓ 1.0 → 2.0 → | A A |
| $I^{2}t$ for fusing (t = 8.3mS) max. | I ² t | ←──── 5.0 ─── | A ² S |
| Forward voltage drop max. @ I _F = 1.0A, $T_j = 25^{\circ}C$ | VF | ←──── 1.1 ───→ | v |
| Reverse current max. @ V _{RWM} , $T_j = 25^{\circ}C$ @ V _{RWM} , $T_j = 100^{\circ}C$ | I _R I _R | $\begin{array}{c} \bullet & 0.5 \\ \bullet & 25 \end{array} \xrightarrow{} aaaaaaaaaaaaaaaaaaaaaaaaa$ | μΑ μΑ |
| Reverse recovery time max. 0.5A IF to 1.0A IR. Recovers to 0.25A IRR. | t _{rr} | ← 2.0 → | μS |
| Junction capacitance typ. @ $V_R = 5V$, $f = 1MHz$ | Cj | ← 23 → | ρF |
| Thermal resistance - junction to lead Lead length = 0.375" Lead length = 0" | Rojl Rojl | $\begin{array}{c} & 36 \\ \hline & 7 \\ \hline \end{array}$ | °C/W °C/W |
| Thermal resistance - junction to amb. on 0.06" thick pcb. 1 oz. copper. | Røja | ←−−−−− 95 −−−−→ | °C/W |

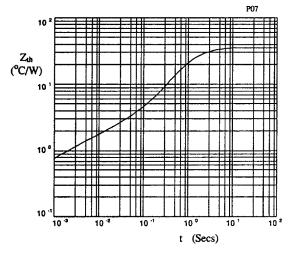


Fig 1. Transient thermal impedance characteristic.

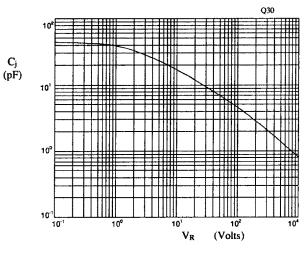
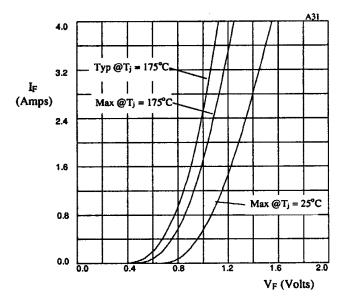


Fig 2. Typical junction capacitance as a function of reverse voltage.

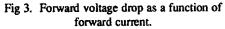
RECTIFIER, up to 1kV, 2A, 2µs

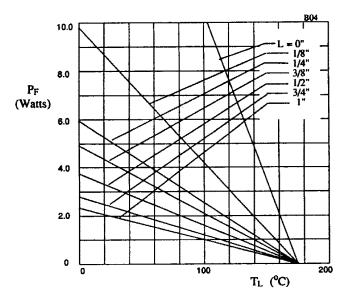
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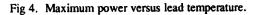
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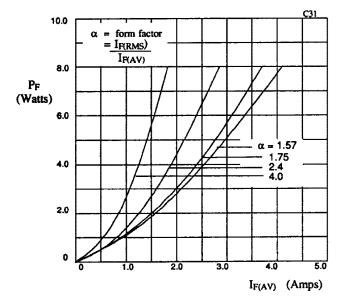


Fig 5. Forward power dissipation as a function of forward current, for sinusoidal operation.

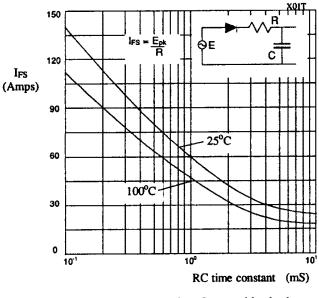


Fig 6. Maximum ratings for capacitive loads.